

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".cls.	US-PGPUB; USPAT	OR	ON	2005/11/25 17:36
L1	3742	257/774	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:21
L2	3108	257/773	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:21
L3	1948	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:22
L4	585	257/770	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
L5	1819	257/750	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
L6	5222	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
L7	1363	257/763	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24

L8	2395	438/706	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
S1	2	("20050085086").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:05
S2	1052	257/734.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/25 15:57
S3	811	S2 and @ad<="20031021"	US-PGPUB; USPAT	OR	ON	2005/11/25 16:59
S4	453	S3 and via	US-PGPUB; USPAT	OR	ON	2005/11/25 17:26
S5	100	S3 and via and gate	US-PGPUB; USPAT	OR	ON	2005/11/25 17:28
S6	6682	via near hole and gate	US-PGPUB; USPAT	OR	ON	2005/11/25 17:29
S7	3528	via near hole and gate and semiconductor near device	US-PGPUB; USPAT	OR	ON	2005/11/25 17:30
S8	0	via near hole and gate and semiconductor near device and silicon near laye and substrate and dielectric and metal	US-PGPUB; USPAT	OR	ON	2005/11/25 17:30
S9	20751	((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal	US-PGPUB; USPAT	OR	ON	2005/11/25 17:36
S10	14801	((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas.	US-PGPUB; USPAT	OR	ON	2005/11/25 17:37
S11	13023	((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. and @ad<="20031021"	US-PGPUB; USPAT	OR	ON	2005/11/25 17:37
S12	1892	(via near hole) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. and @ad<="20031021"	US-PGPUB; USPAT	OR	ON	2005/11/25 17:37
S13	1	("6791187").PN.	US-PGPUB; USPAT	OR	OFF	2005/11/28 13:19

S14	0	("1761481986").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2005/11/28 13:19
S15	2	("0176148").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:20
S16	0	(176148/1986).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:20
S17	0	("1761481986").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:20
S18	0	"1761481986"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 13:21
S19	7	176148/1986	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 13:47
S20	100	tapered near via near hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 13:47
S21	62	tapered near via near hole	US-PGPUB; USPAT	OR	ON	2005/11/28 13:50
S22	7	tapered near via near hole and anisotropically	US-PGPUB; USPAT	OR	ON	2005/11/28 16:20